

Laboratory of Atomic

nd Solid State Physics

# Characterization of 128x128 MM-PAD-2.1 ASIC : A Fast Framing Hard X-ray Detector

Divya Gadkari<sup>a</sup>, Katherine S. Shanks<sup>b</sup>, Hannah Hu<sup>c</sup>, Hugh T. Philipp<sup>a</sup>, Mark W. Tate<sup>a</sup>,

Julia Thom-Levy<sup>a</sup>, Sol M. Gruner<sup>a,b</sup>

<sup>a</sup>Department of Physics, Cornell University, Ithaca, NY ,USA; <sup>b</sup>CHESS, Cornell University, Ithaca, NY 14853, USA; <sup>c</sup>University of Chicago, Chicago, IL, USA



### Abstract

Modern direct detection Pixel Array Detectors are built around **MODULES** consisting of an x-ray **SENSOR** bonded pixel-by-pixel to an Application Specific Integrated Circuit (**ASIC**). The sensor, typically of Si or CdTe, absorbs x-rays resulting in mobile charges; these are conveyed to the ASIC, each pixel of which has its own processing electronics. A full detector consists of an array of modules, control electronics, operating system and associated hardware in an appropriate housing. We characterize a new x-ray Mixed-Mode Pixel Array Detector (MM-PAD-2.1) ASIC developed at Cornell. Using an integrating pixel front-end with dynamic charge removal architecture, the MM-PAD-2.1 ASIC extends the maximum measurable x-ray signal (in 20 keV photon units) to > 10<sup>7</sup> x-rays/pixel/frame while maintaining a low read noise across the full dynamic range, all while imaging continuously at a frame rate of up to 10 kHz. We use both laboratory x-ray sources and the Cornell High Energy Synchrotron Source (CHESS) to characterize two single ASIC prototype detectors for both low (single x-ray) and high incident flux detector used a 750 µm thick CdTe sensor for x-rays above ~ 20 keV.

## 3. In-house Characterization

## 4. Characterization at CHESS



1. Motivation

- Synchrotron x-ray facilities moving towards higher energies, high repetition rate, increased brilliance
- Developing x-ray detectors with :
  > Wide dynamic range
  > High stopping power for x-rays of in the 20 to
  > 100 keV range

Characterization of modules with 500  $\mu m$  thick Si and 750  $\mu m$  thick CdTe sensors



- Measured gain, using pinhole x-ray scan, and read noise :
- ≻ GCdTe/GSi = 0.74±0.01
- SNR ≥ 2 for x-ray energies > 5 keV (Si) & 8 keV (CdTe)



- Performance of CdTe MM-PAD 2.1 measured at CHESS
- Incident energy of 61.332 keV



- Incident flux of << 1 x-rays/frame for 99% of pixels, ~2 x-rays for rest
- CdTe exhibits fluorescence at
   23.2 keV (Cd) and 27.5 keV (Te)



> High frame rate
> Low noise







MM-PAD-2.1 is based on existing MM-PAD-1 design

- Spatial resolution measured using Edge Spread Function (ESF) (response to step function)
- Measured charge cloud size of :
- > 20 μm in Si
  > 20 μm in CdTe at 26 kV tube bias
  > 30 μm in CdTe at 47 kV tube bias



- CdTe known to polarize under high flux
- Count rate deficit
   Worsened image uniformity
   Lateral movement of charg
- Incident flux varied using steel attenuators
- Polarization at accumulated doses of 10<sup>11</sup> keV/mm<sup>2</sup> and above

#### 5. Conclusions

- 128x128 pixels/module
  Two-stage adaptive gain (40 fF, 880 fF)
- Dual track-and-hold circuit
- Dual in-pixel counters
   Divided into 16 banks

	MM-PAD-1	MM-PAD-2.1
	(8  keV equivalent)	(20  keV equivalent)
Format	$128 \times 128$	$128 \times 128$
Pixel pitch	$150 \ \mu m$	$150 \ \mu m$
Sensor	Si,CdTe	Si,CdTe
Charge Collection	holes only	electrons or holes
Frame rate $(FR)$	$1.1 \mathrm{~kHz}$	10  kHz
Duty Cycle, max FR	0%	99%
Read noise	0.16 photon	0.13 photon
Well capacity	$4.7 \times 10^7$ photons	$2.2 \times 10^7$ photons
Instantaneous count rate	$> 10^{12} \mathrm{~ph/pix/s}$	$> 10^{12}~{ m ph/pix/s}$
Sustained count rate	$4{\times}10^8~{\rm ph/pix/s}$	$> 3{ imes}10^{10}~{ m ph/pix/s}$

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- Incident beam spanning 12x8 (FWHM) pixels, source intensity varying at 360 Hz
- Frame rate of 9.9 kHz
   Fast fourier transform (FFT) of measured signal vs frame number yields 361 ± 1 Hz

• The MM-PAD-2.1 ASIC extends x-ray detector capabilities well beyond the current state-of-theart.

The MM-PAD-2.1 ASIC is a proof-of-concept. A commercially robust ASIC is being developed by Cornell University in collaboration with Sydor Technologies under a DOE grant.
Sydor's plans include 512x512 and 1kx1k pixel versions, with Si and CdTe sensors.